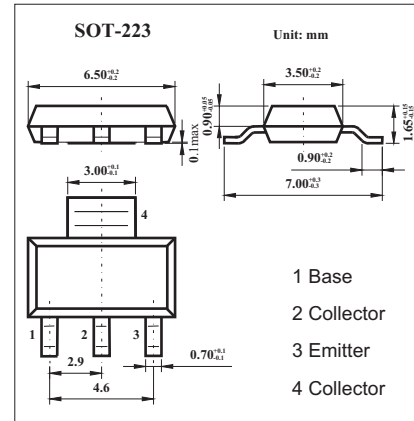


NPN General Purpose Amplifier

PZTA06

■ Features

- Power dissipation: $P_c=1W$
- Collector current (DC): $I_c=500mA$
- Complementary PNP Type Available (PZTA56)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	80	V
Collector-emitter voltage	V_{CEO}	80	V
Emitter-base voltage	V_{EBO}	4	V
Collector current	I_c	500	mA
Total Device Dissipation Alumina Substrate	P_c	1	W
Junction and Storage Temperature	T_J, T_{stg}	-55 to 150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c = 100\mu A, I_E = 0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c = 1.0 mA, I_B = 0$	80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_c = 0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=80 V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_c=0$			0.1	μA
DC current gain *	h_{FE}	$I_c = 10 mA, V_{CE} = 1.0 V$ $I_c = 100 mA, V_{CE} = 1.0 V$	100 100			
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_c = 100 mA, I_B = 10 mA$			0.25	V
Base-Emitter On Voltage	$V_{BE(sat)}$	$I_c = 100 mA, V_{CE} = 1.0 V$			1.2	V
Transition frequency	f_T	$I_c = 10 mA, V_{CE} = 2V, f = 100 MHz$	100			MHz

* Pulse test: pulse width $\leq 300 \mu s$, duty cycle $\leq 2.0\%$.

■ Marking

Marking	A06
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